

R-C Thermal Model Parameters

DESCRIPTION

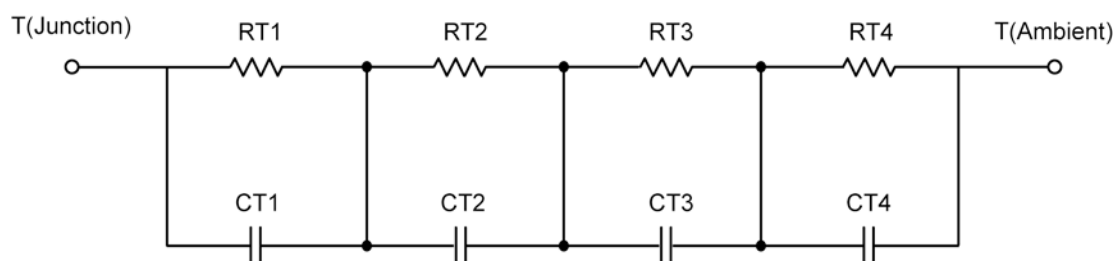
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

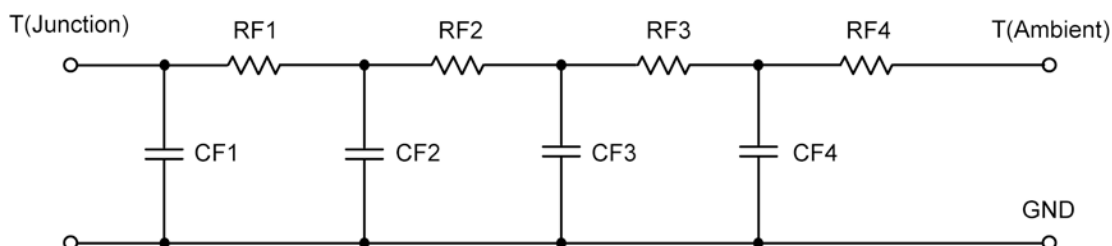
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	20.8369	N/A	4.0258
RT2	6.2505	N/A	9.8468
RT3	16.9980	N/A	6.3637
RT4	40.9146	N/A	4.7637
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	349.7413 m	N/A	249.2939 m
CT2	471.3850 u	N/A	13.2421 m
CT3	20.7626 m	N/A	1.7311 m
CT4	2.6297	N/A	138.5637 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	6.4674	N/A	5.8106
RF2	17.7225	N/A	6.5174
RF3	22.8037	N/A	7.9891
RF4	38.0064	N/A	4.6829
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	445.9950 u	N/A	132.2512 u
CF2	17.6947 m	N/A	1.5505 m
CF3	244.3088 m	N/A	9.2501 m
CF4	2.3330	N/A	117.6707 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

